

<p>FORM PTO-1449 (SUBSTITUTE)</p> <p>U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE</p> <p>INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))</p>	<p>Attorney Docket No.: CIP of Applic. No. GR 98 P 1801 09/232,081</p> <p style="text-align: right;"><i>Ser No: 09/363277</i></p> <p>Applicant Kai Wurster et al.</p> <hr/> <p>Filing Date of CIP Group Art Unit July 28, 1999 <i>281T 2812</i></p>
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EXAMINER INITIALS	PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
<i>gm</i>	A	5,187,550	02/93	Yanagisawa		
<i>gm</i>	B	5,670,805	09/97	Hammerl et al.		
<i>gm</i>	C	4,937,205	06/90	Nakayama et al.		
<i>gm</i>	D	5,344,381	09/94	Cabrera y Lopez Caram		
<i>gm</i>	E	5,336,912	08/94	Ohtsuki		
<i>gm</i>	F	5,360,758	11/94	Bronner et al.		
<i>gm</i>	G	5,250,829	10/93	Bronner et al.		
	H					
	I					

FOREIGN PATENT DOCUMENT

DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES	TRANSL. NO
<i>gm</i>	J	0 621 632 A1	10/94	Europe		X
	K					
	L					
	M					
	N					

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

<i>gm</i>	"Shallow n <sup>+</sup> Junctions in Silicon by Arsenic Gas-Phase Doping" (Ransom et al.), Journal of the Electrochemical Society, Vol. 141, No. 5, pages 1378-1381;
<i>gm</i>	"Low Pressure Deposition of Doped SiO <sub>2</sub> by Pyrolysis of Tetraethylorthosilicate (TEOS) (Becker), Journal of the Electrochemical Society, Vol. 136, No. 10, pages 3033-3043.

EXAMINER <i>Jennifer M. Kennedy</i>	DATE CONSIDERED <i>1/2/2002</i>
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

FORM PTO-1449 (SUBSTITUTE)				Attorney Docket No.: GR 98 P 1801		CIP of Applic. No. 09/232,081 <b>Ser No: 09/343277</b>	
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE				Applicant Kai Wurster et al.			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))				Filing Date of CIP July 28, 1999		Group Art Unit <del>2811</del> <b>2812</b>	

  

EXAMINER INITIALS	A	PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A						
	B						
	C						
	D						
	E						
	F						
	G						
	H						
	I						

  

**FOREIGN PATENT DOCUMENT**

	J	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES   NO	
	J							
	K							
	L							
	M							
	N							

  

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)**

gk		"0.228μm <sup>2</sup> Trench Cell Technologies with Bottle-Shaped Capacitor for 1Gbit DRAMs" (Ozaki et al.), IEDM 95, pages 661-664.

  

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